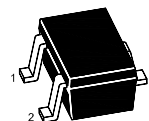


# NPN Silicon Epitaxial Planar Transistor

The transistor is subdivided into three groups Q, R and S according to its DC current gain.



1.Base 2.Emitter 3.Collector  
SOT-323 Plastic Package

## Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	60	V
Collector Emitter Voltage	$V_{CEO}$	50	V
Emitter Base Voltage	$V_{EBO}$	7	V
Collector Current	$I_C$	150	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

## Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 6\text{ V}$ , $I_C = 1\text{ mA}$ Current Gain Group	Q $h_{FE}$	120	-	270	-
	R $h_{FE}$	180	-	390	-
	S $h_{FE}$	270	-	560	-
Collector Base Cutoff Current at $V_{CB} = 60\text{ V}$	$I_{CBO}$	-	-	0.1	$\mu\text{A}$
Emitter Base Cutoff Current at $V_{EB} = 7\text{ V}$	$I_{EBO}$	-	-	0.1	$\mu\text{A}$
Collector Base Breakdown Voltage at $I_C = 50\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E = 50\text{ }\mu\text{A}$	$V_{(BR)EBO}$	7	-	-	V
Collector Emitter Saturation Voltage at $I_C = 50\text{ mA}$ , $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	-	0.4	V
Transition Frequency at $V_{CE} = 12\text{ V}$ , $-I_E = 2\text{ mA}$ , $f = 100\text{ MHz}$	$f_T$	-	180	-	MHz
Collector Output Capacitance at $V_{CB} = 12\text{ V}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	2	3.5	pF

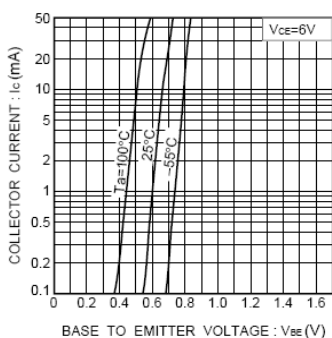


Fig.1 Grounded emitter propagation characteristics

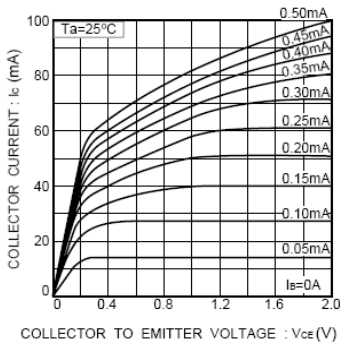


Fig.2 Grounded emitter output characteristics ( I )

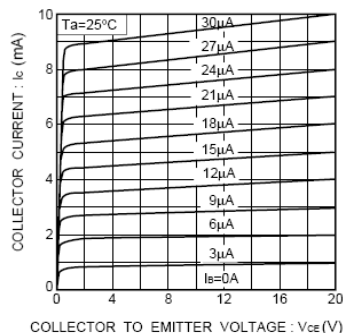


Fig.3 Grounded emitter output characteristics ( II )

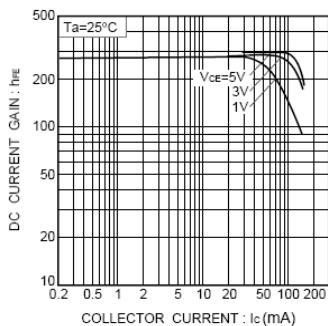


Fig.4 DC current gain vs. collector current ( I )

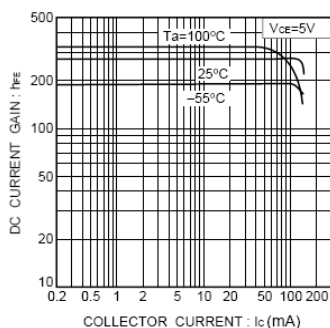


Fig.5 DC current gain vs. collector current ( II )

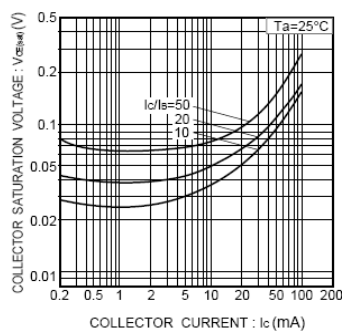


Fig.6 Collector-emitter saturation voltage vs. collector current

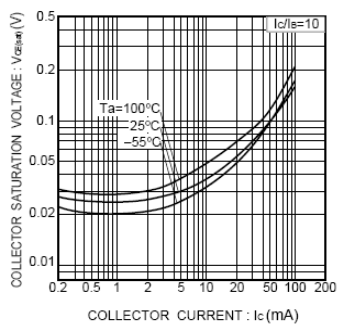


Fig.7 Collector-emitter saturation voltage vs. collector current ( I )

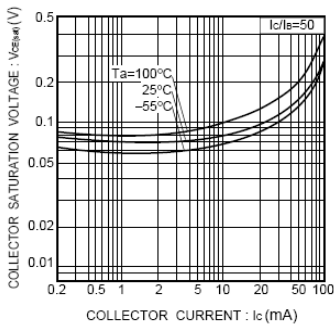


Fig.8 Collector-emitter saturation voltage vs. collector current (II)

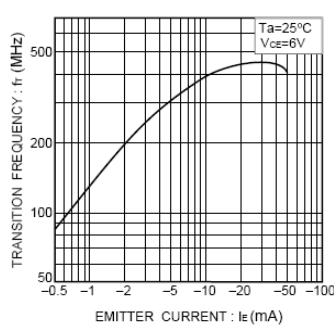


Fig.9 Gain bandwidth product vs. emitter current

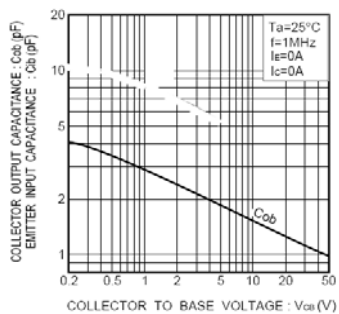


Fig.10 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

## **SOT-323 Package outline dimensions**

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